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Attorney Docket No. 5649-874

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Hag-ju Cho
Serial No.: 09/893,035 ✓
Filed: June 27, 2001

Confirmation No. 3421
Examiner: Erik J. Kielin
Group Art Unit: 2813

For: METHODS OF MANUFACTURING INTEGRATED CIRCUIT DEVICES
THAT INCLUDE A METAL OXIDE LAYER DISPOSED ON ANOTHER
LAYER TO PROTECT THE OTHER LAYER FROM DIFFUSION OF
IMPURITIES AND INTEGRATED CIRCUIT DEVICES MANUFACTURED
USING SAME

Date: January 30, 2003

BOX RCE
Commissioner for Patents
Washington, DC 20231

AMENDMENT ACCOMPANYING RCE

Sir:

This Amendment is responsive to the Final Official Action of October 2, 2002 and the Advisory Action of January 16, 2003. Pursuant to the rules for amendments under 37 C.F.R. § 1.121, the claims have been amended herein using the rewritten claims format. The present amendment also includes a section entitled "**VERSION WITH MARKINGS TO SHOW CHANGES MADE**" attached hereto.

In the claims:

Please enter amended Claim 1 as follows:

C1

1. (Amended) A method of manufacturing an integrated circuit device, comprising:

forming an insulation layer that comprises oxygen between upper and lower conductive layers, the insulation layer having a first surface portion that is exposed by the upper and lower conductive layers and a second, non-exposed, surface portion; and

exposing the insulation layer to a metal precursor that is reactive with oxygen so as to form a first metal oxide layer on the first surface portion of the insulation layer without forming the first metal oxide layer on the second surface portion of the insulation layer, such that the first metal oxide layer and the second surface portion of the insulation layer do not overlap.

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